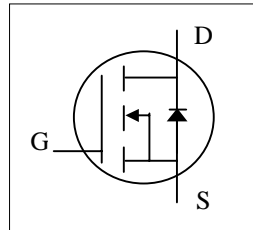




- ▼ **Low Gate Charge**
- ▼ **Fast Switching Characteristics**
- ▼ **Simple Drive Requirement**
- ▼ **RoHS Compliant**

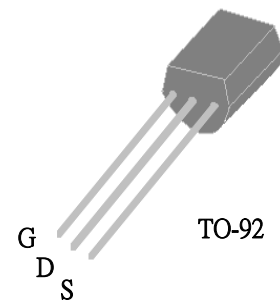


BV_{DSS}	650V
$R_{DS(ON)}$	12 Ω
I_D	160mA

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The TO-92 package is universally used for all commercial-industrial applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	160	mA
$I_D @ T_A = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	100	mA
I_{DM}	Pulsed Drain Current ¹	300	mA
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	0.83	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal Resistance Junction-ambient	Max. 150	$^\circ C/W$



AP01L60T

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	650	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.8	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =0.5A	-	-	12	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =0.5A	-	0.8	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =600V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =480V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±30V	-	-	±100	nA
Q _g	Total Gate Charge ³	I _D =100mA	-	7	11	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	1.4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	3.4	-	nC
t _{d(on)}	Turn-on Delay Time ³	V _{DD} =300V	-	8	-	ns
t _r	Rise Time	I _D =1A	-	5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω, V _{GS} =10V	-	13	-	ns
t _f	Fall Time	R _D =300Ω	-	9	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	260	420	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	20	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	3	-	pF
R _g	Gate Resistance	f=1.0MHz	-	3	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ³	I _S =160mA, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =1A, V _{GS} =0V,	-	290	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	870	-	nC

Notes:

- 1.Pulse width limited by safe operating area.
- 3.Pulse width ≤300us , duty cycle ≤2%.

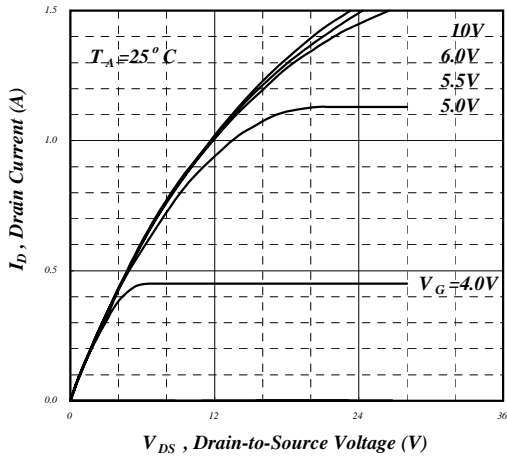


Fig 1. Typical Output Characteristics

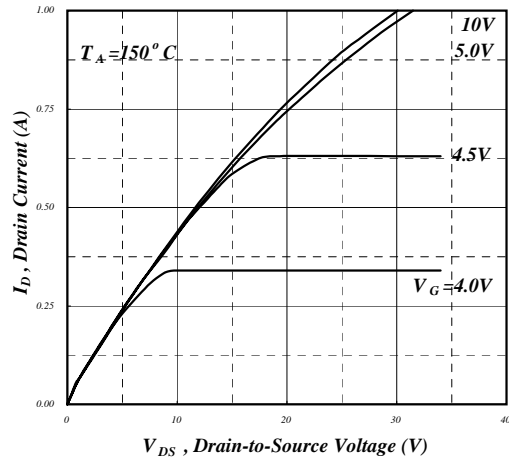


Fig 2. Typical Output Characteristics

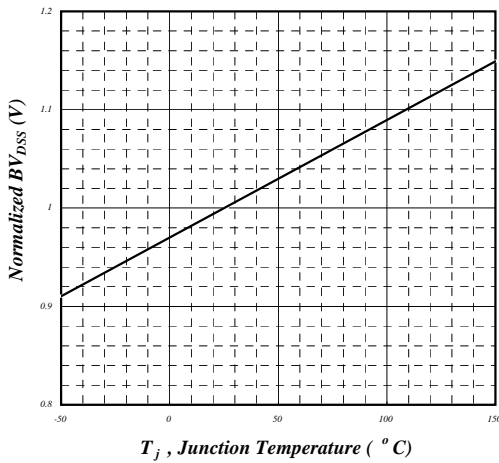


Fig 3. Normalized BV_{DS} v.s. Junction Temperature

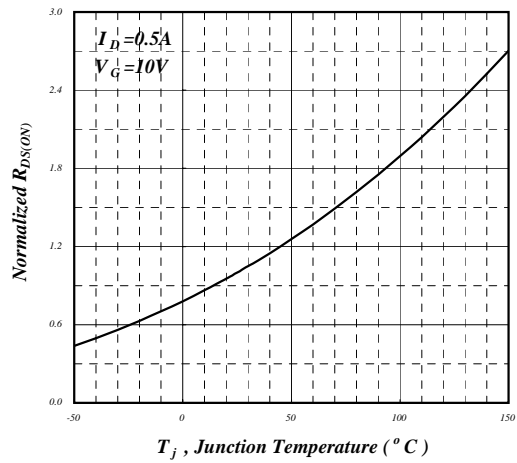


Fig 4. Normalized On-Resistance v.s. Junction Temperature

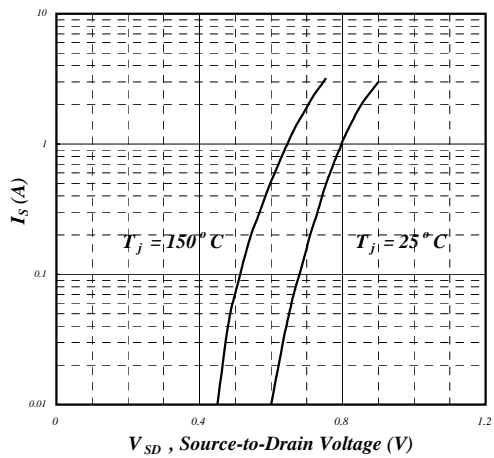


Fig 5. Forward Characteristic of Reverse Diode

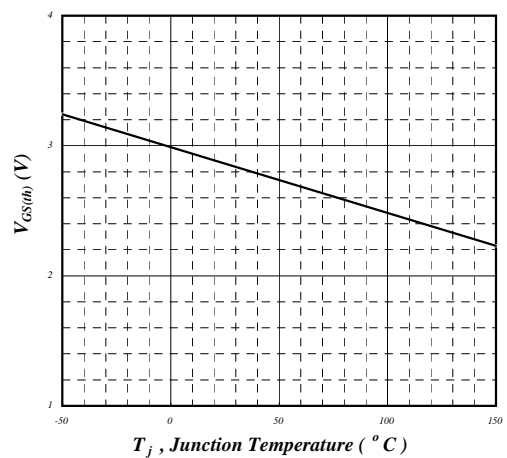


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

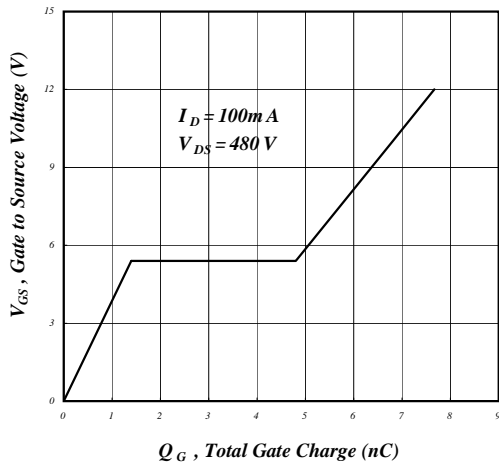


Fig 7. Gate Charge Characteristics

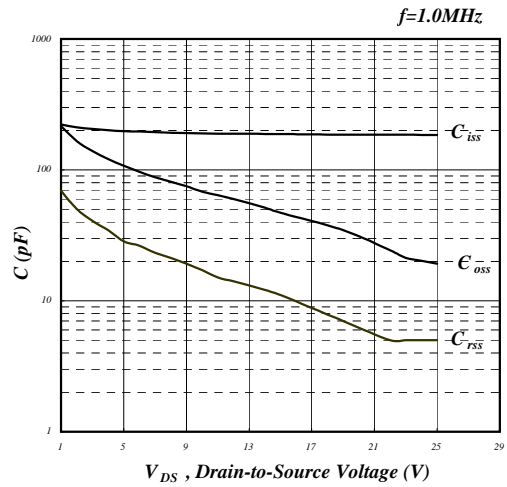


Fig 8. Typical Capacitance Characteristics

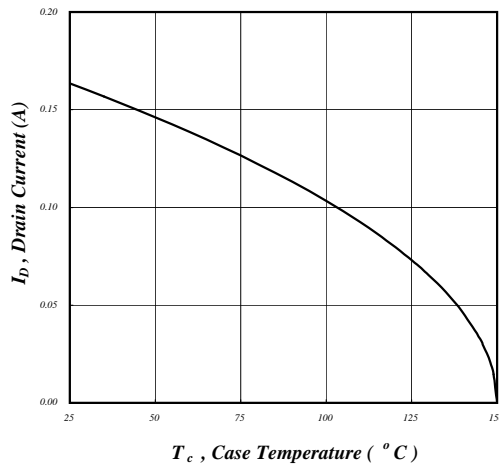


Fig 9. Maximum Drain Current v.s. Case Temperature

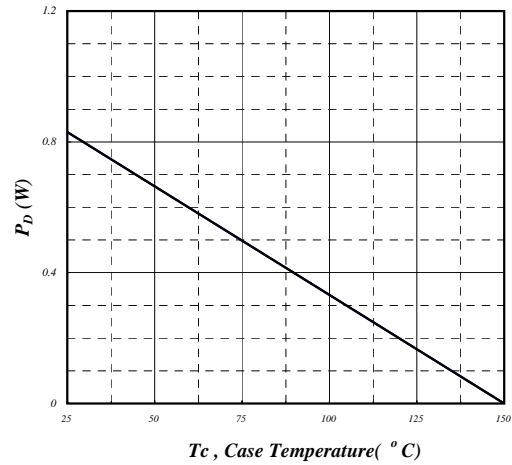


Fig 10. Typical Power Dissipation

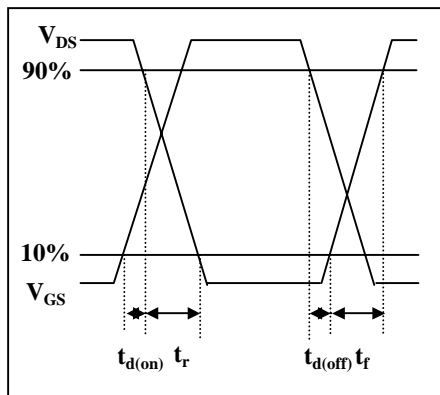


Fig 11. Switching Time Waveform

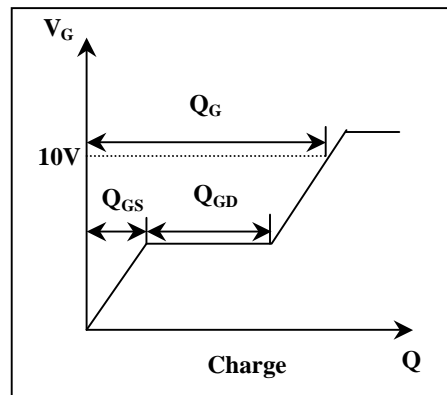


Fig 12. Gate Charge Waveform